

#### **New Product**

# N-Channel 30-V (D-S) 175°C MOSFET

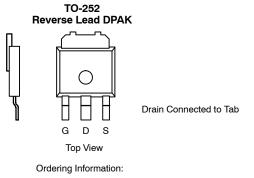
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A) <sup>b</sup>		
30	0.0065 @ V <sub>GS</sub> = 10 V	84 <sup>b</sup>		
	0.0095 @ V <sub>GS</sub> = 4.5 V	59 <sup>b</sup>		

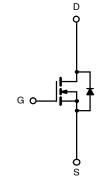
#### **FEATURES**

- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- Optimized for Low-Side Synchronous Rectifier Operation
- 100% R<sub>g</sub> Tested

#### **APPLICATIONS**

- DC/DC Converters
  - Desktop CPU Core
- Synchronous Rectifiers





Ordering Information:
SUR50N03-06P—E3
SUR50N03-06P-T4—E3 (altrenate tape orientation)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (TA = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	,,	
Gate-Source Voltage		V <sub>GS</sub>	±20		
	T <sub>A</sub> = 25°C		27		
Continuous Drain Current	T <sub>C</sub> = 25°C	I <sub>D</sub>	84 <sup>b</sup>		
	T <sub>C</sub> = 100°C		59 <sup>b</sup>	A	
Pulsed Drain Current		I <sub>DM</sub>	100		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	25		
	T <sub>C</sub> = 25°C	_	88		
Maximum Power Dissipation	T <sub>A</sub> = 25°C	P <sub>D</sub>	8.3 <sup>a</sup>	w	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 sec	R <sub>thJA</sub>	15	18	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		40	50	
Maximum Junction-to-Case		R <sub>thJC</sub>	1.4	1.7	

#### Notes

- a. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- b. Based on maximum allowable junction temperature, package limitation current is 50 A.

# Vishay Siliconix

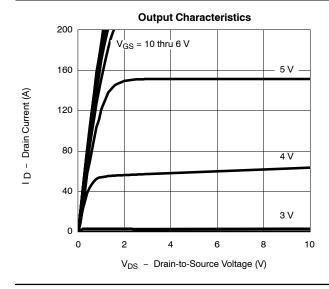
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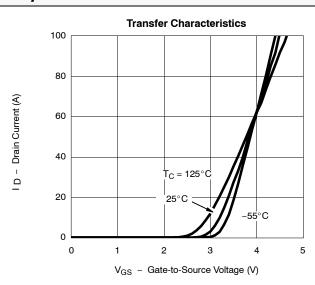


SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit	
Static	•		•	1			
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	30			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0		3.0		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = $\pm 20$ V			±100	nA	
7 0 1 1/1   10 1 0 1		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	DSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125^{\circ}\text{C}$			50	μΑ	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	50			Α	
		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.0053	0.0065		
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125°C			0.0105	Ω	
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0078	0.0095		
Forward Transconductance <sup>b</sup>	9fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	20			S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			3100		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		565			
Reverse Transfer Capacitance	C <sub>rss</sub>			255			
Gate Resistance	R <sub>g</sub>		1	1.9	3.1	Ω	
Total Gate Charge <sup>c</sup>	Qg			21	30	nC	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 15 \text{ V}, \ V_{GS} = 4.5 \text{ V}, \ I_D = 50 \text{ A}$		10			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			7.5			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			12	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 0.3 $\Omega$		12	20	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		30	45		
Fall Time <sup>c</sup>	t <sub>f</sub>			10	15		
Source-Drain Diode Ratings and	d Characteristi	c (T <sub>C</sub> = 25°C)					
Pulsed Current	I <sub>SM</sub>				100	Α	
Diode Forward Voltageb	V <sub>SD</sub>	I <sub>F</sub> = 100 A, V <sub>GS</sub> = 0 V		1.2	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = 50 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		35	70	ns	

- Guaranteed by design, not subject to production testing. Pulse test; pulse width  $\leq 300~\mu s$ , duty cycle  $\leq 2\%$ . Independent of operating temperature.

#### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





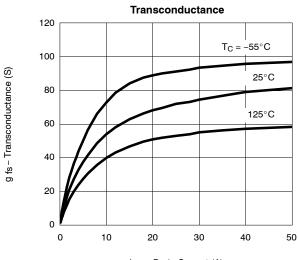




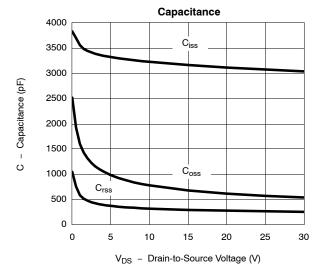


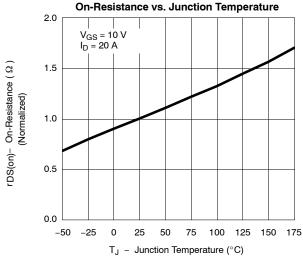
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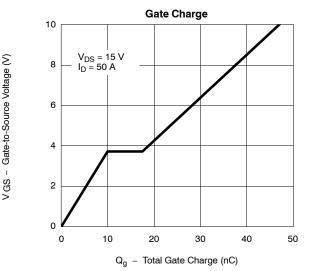


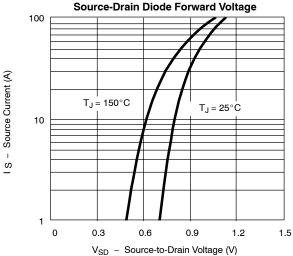




On-Resistance vs. Drain Current 0.0150 0.0125 rDS(on)- On-Resistance (  $\Omega$  ) 0.0100 V<sub>GS</sub> = 4.5 V 0.0075  $V_{GS} = 10 \text{ V}$ 0.0050 0.0025 0.0000 0 20 40 60 80 100

I<sub>D</sub> - Drain Current (A)



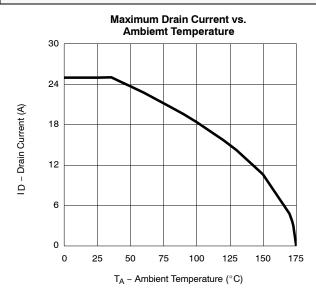


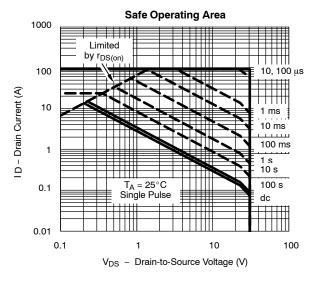
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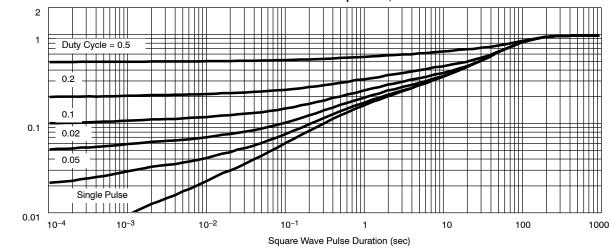


#### THERMAL RATINGS

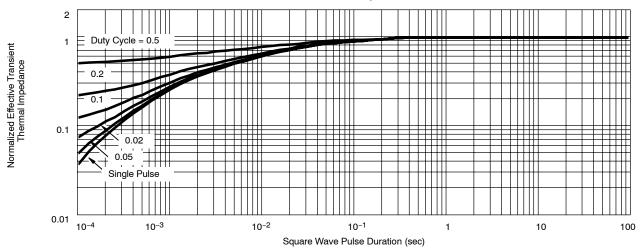




#### Normalized Thermal Transient Impedance, Junction-to-Ambient



#### Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Effective Transient Thermal Impedance

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